

RJK5033DPP-M0

Silicon N Channel MOS FET
High Speed Power Switching

R07DS0205EJ0100

Rev.1.00

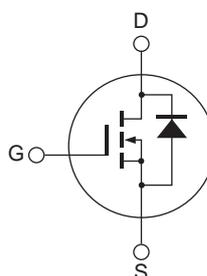
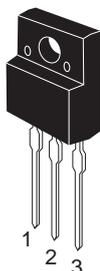
Nov 29, 2010

Features

- Low on-state resistance
 $R_{DS(on)} = 0.96 \Omega$ typ. (at $I_D = 3 A$, $V_{GS} = 10 V$, $T_a = 25^\circ C$)
- High speed switching

Outline

RENESAS Package code: PRSS0003AF-A
(Package name: TO-220FL)



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings

($T_a = 25^\circ C$)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DSS}	500	V
Gate to source voltage	V_{GSS}	± 30	V
Drain current	I_D	6	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	24	A
Avalanche current	I_{AP} ^{Note3}	6	A
Channel dissipation	P_{ch} ^{Note 2}	27.4	W
Channel to case thermal Impedance	θ_{ch-c}	4.56	$^\circ C/W$
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

Notes: 1. Pulse width limited by safe operating area.

2. Value at $T_c = 25^\circ C$

3. $ST_{ch} = 25^\circ C$, $T_{ch} \leq 150^\circ C$

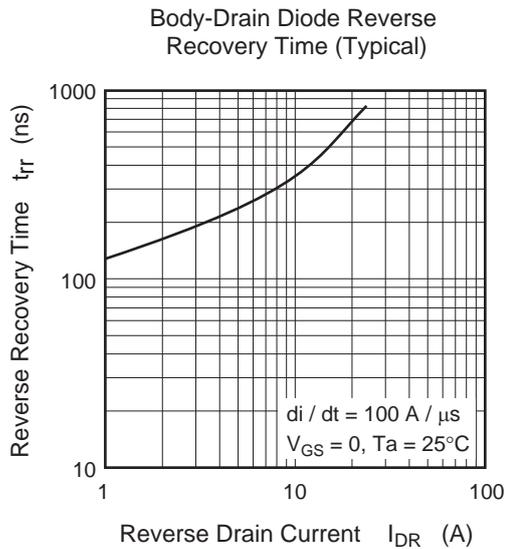
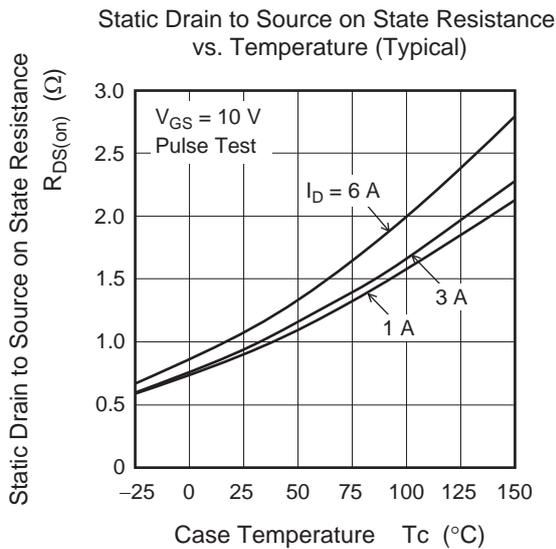
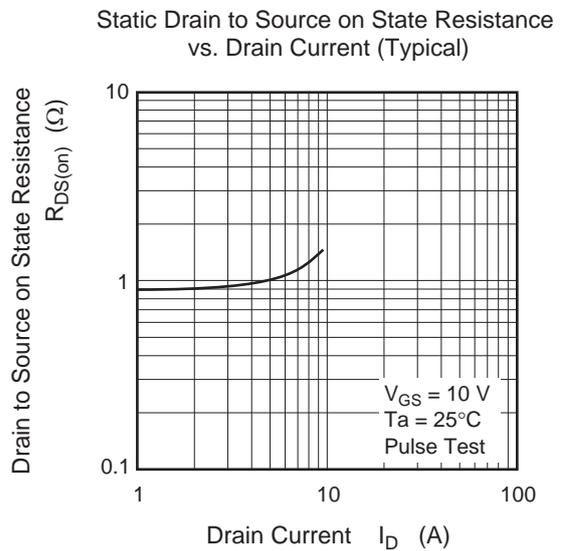
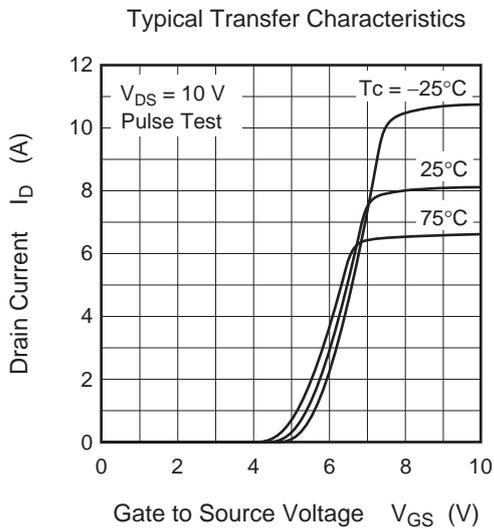
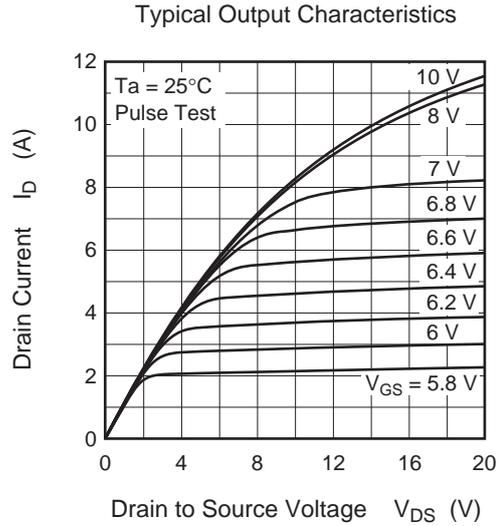
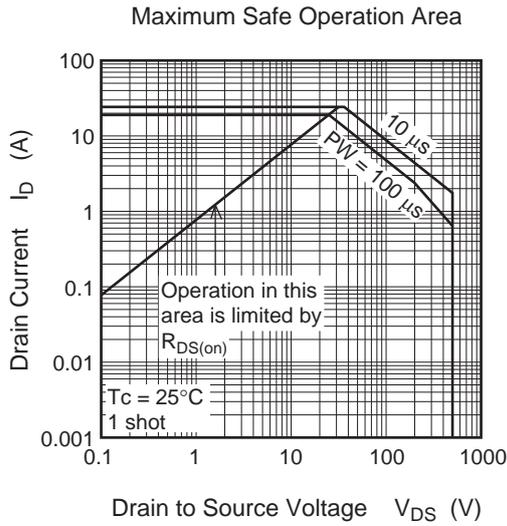
Electrical Characteristics

(Ta = 25°C)

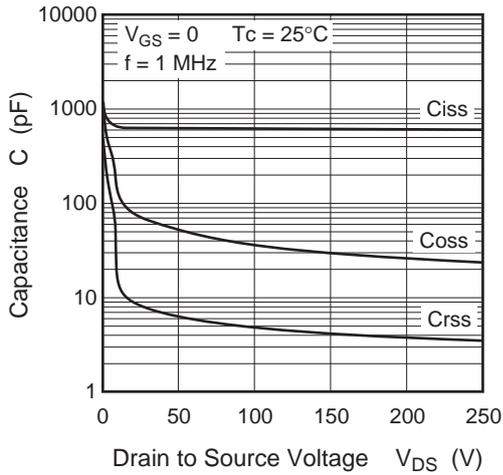
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	$I_D = 1 \text{ mA}$, $V_{GS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 500 \text{ V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.5	—	4.5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.96	1.3	Ω	$I_D = 3 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note 4}
Input capacitance	C_{iss}	—	600	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	C_{oss}	—	70	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	10	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	$V_{DD} = 200 \text{ V}$
Rise time	t_r	—	20	—	ns	$I_D = 3 \text{ A}$
Turn-off delay time	$t_{d(off)}$	—	90	—	ns	$V_{GS} = 10 \text{ V}$
Fall time	t_f	—	30	—	ns	$R_g = 10 \Omega$
Body-drain diode forward voltage	V_{DF}	—	0.9	1.5	V	$I_F = 6 \text{ A}$, $V_{GS} = 0$ ^{Note 4}
Body-drain diode reverse recovery time	t_{rr}	—	250	—	ns	$I_F = 6 \text{ A}$, $V_{GS} = 0$ $V_{DD} = 250 \text{ V}$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note: 4. Pulse test

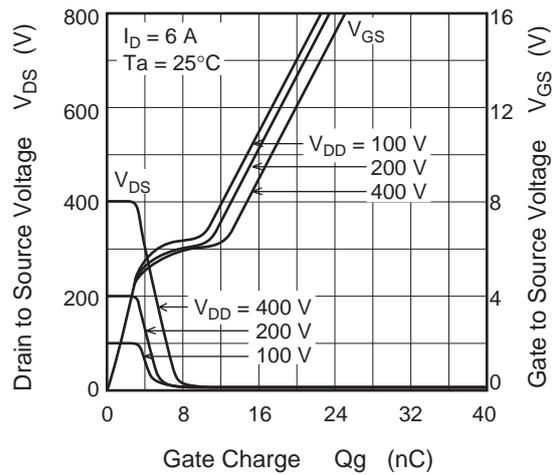
Main Characteristics



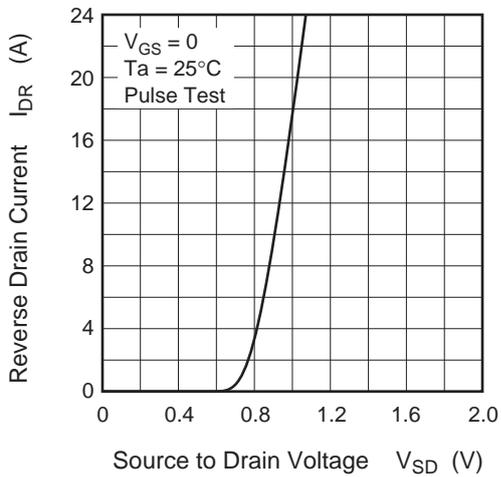
Typical Capacitance vs. Drain to Source Voltage



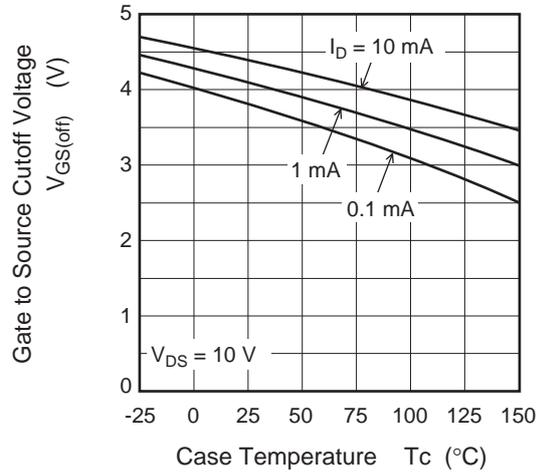
Dynamic Input Characteristics (Typical)



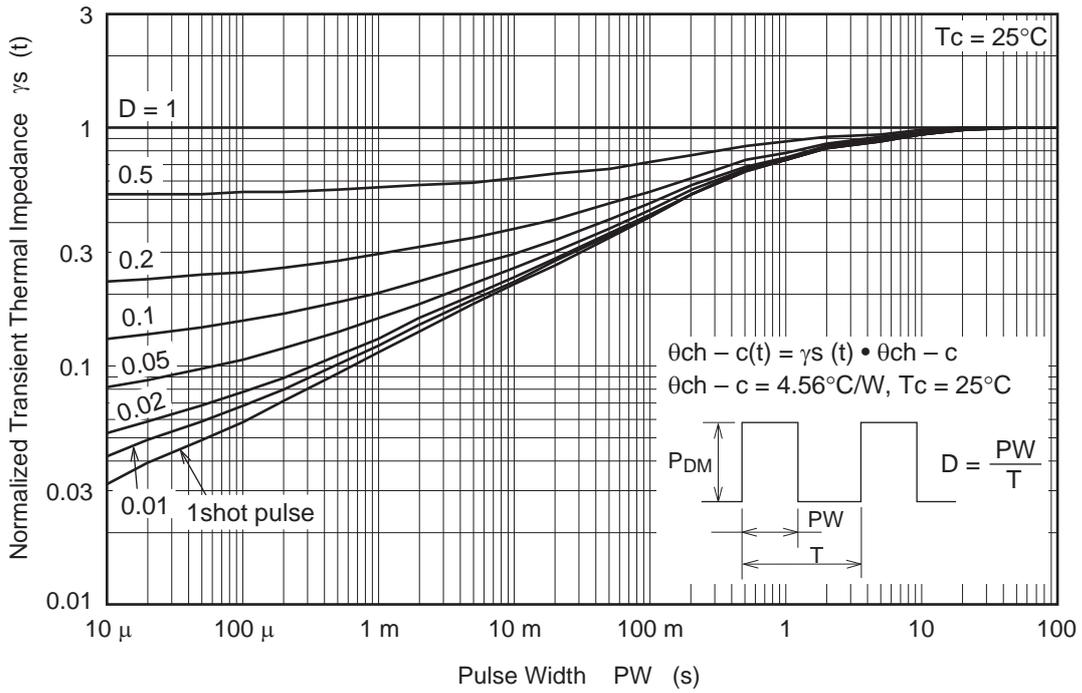
Reverse Drain Current vs. Source to Drain Voltage (Typical)



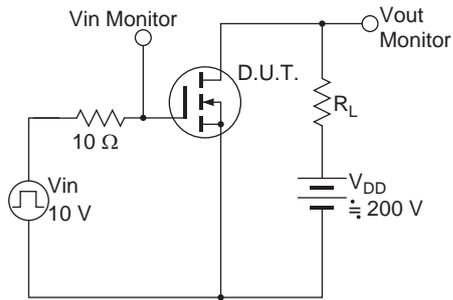
Gate to Source Cutoff Voltage vs. Case Temperature (Typical)



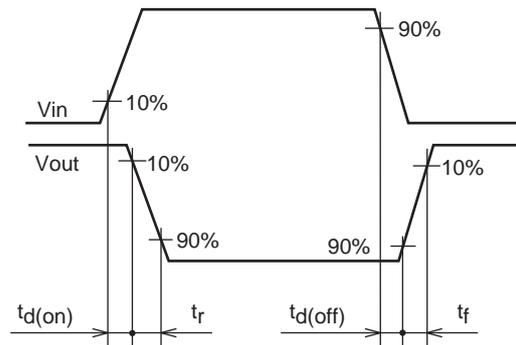
Normalized Transient Thermal Impedance vs. Pulse Width



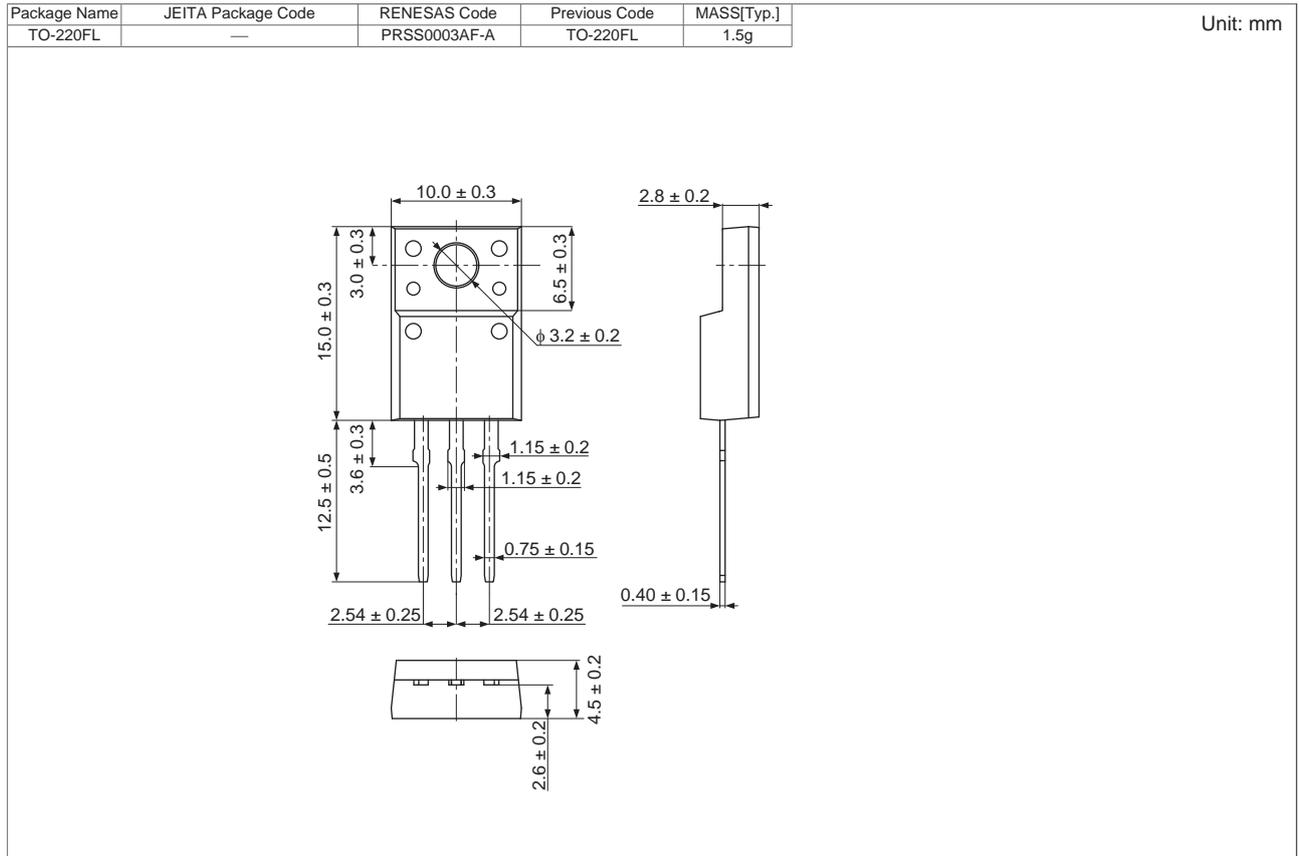
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJK5033DPP-M0-T2	1050 pcs	Box (Tube)

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